

## Deep levels roles in non-equilibrium conductivity in irradiated Si.

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Two light beams excitation technique was used for investigation the recombination process in the by neutron irradiated Si (WODEAN samples, bar type). By application of additional illumination in the extrinsic excitation region the photoconductivity spectrum and time dependent conductivity measurement reveals the levels that participate in the photoconductivity, but, if the sample is excited, their excitation quenched the photoresponse. These results allow to analyze the properties of micro-inhomogeneities identified by Hall effects, thermally stimulated and persistent current measurements.

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